# NTMFS5832NL

# Power MOSFET
## 40 V, 111 A, 4.2 mΩ

**Features**

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

**MAXIMUM RATINGS** ($T_J$ = 25°C unless otherwise stated)

| Parameter | | | Symbol | Value | Unit |
|---|---|---|---|---|---|
| Drain−to−Source Voltage | | | $V_{DSS}$ | 40 | V |
| Gate−to−Source Voltage | | | $V_{GS}$ | ±20 | V |
| Continuous Drain Current $R_{\theta JA}$ (Note 1) | Steady State | $T_A$ = 25°C | $I_D$ | 20 | A |
| | | $T_A$ = 70°C | | 16 | |
| Power Dissipation $R_{\theta JA}$ (Note 1) | | $T_A$ = 25°C | $P_D$ | 3.1 | W |
| | | $T_A$ = 70°C | | 1.9 | |
| Continuous Drain Current $R_{\theta JC}$ (Note 1) | | $T_C$ = 25°C | $I_D$ | 111 | A |
| | | $T_C$ = 70°C | | 89 | |
| Power Dissipation $R_{\theta JC}$ (Note 1) | | $T_C$ = 25°C | $P_D$ | 96 | W |
| | | $T_C$ = 70°C | | 61 | |
| Pulsed Drain Current | $t_p$ = 10 μs | | $I_{DM}$ | 443 | A |
| Operating Junction and Storage Temperature | | | $T_J$, $T_{STG}$ | −55 to +150 | °C |
| Source Current (Body Diode) | | | $I_S$ | 111 | A |
| Single Pulse Drain−to−Source Avalanche Energy (L = 0.1 mH) | | | EAS | 134 | mJ |
| | | | IAS | 52 | A |
| Lead Temperature for Soldering Purposes (1/8″ from case for 10 s) | | | $T_L$ | 260 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

**THERMAL RESISTANCE MAXIMUM RATINGS**

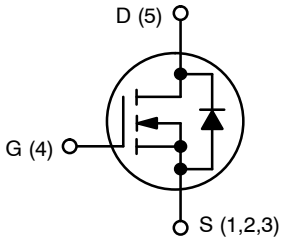
| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Junction−to−Case (Drain) (Note 1) | $R_{\theta JC}$ | 1.3 | °C/W |
| Junction−to−Ambient Steady State (Note 1) | $R_{\theta JA}$ | 40 | |
| Junction−to−Ambient Steady State (Note 2) | $R_{\theta JA}$ | 75 | |

1. Surface−mounted on FR4 board using 1 sq−in pad (Cu area = 1.127 in sq [2 oz] inclusing traces).
2. Surface−mounted on FR4 board using 0.155 in sq (100mm$^2$) pad size.

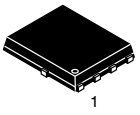
**ON Semiconductor®**

**http://onsemi.com**

| $V_{(BR)DSS}$ | $R_{DS(ON)}$ MAX | $I_D$ MAX |
|---|---|---|
| 40 V | 4.2 mΩ @ 10 V | 111 A |
| | 6.5 mΩ @ 4.5 V | |

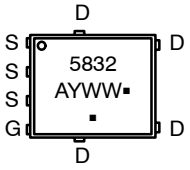



**N−CHANNEL MOSFET**



**DFN5**
**(SO−8FL)**
**CASE 488AA**
**STYLE 1**

**MARKING DIAGRAM**




A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

**ORDERING INFORMATION**

| Device | Package | Shipping† |
|---|---|---|
| NTMFS5832NLT1G | DFN5 (Pb−Free) | 1500/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

**ELECTRICAL CHARACTERISTICS** ($T_J$ = 25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain−to−Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 μA | | 40 | | | V |
| Drain−to−Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | | | | 34.2 | | mV/°C |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 40 V | $T_J$ = 25 °C | | | 1 | μA |
| | | | $T_J$ = 125°C | | | 100 | |
| Gate−to−Source Leakage Current | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ±20 V | | | | ±100 | nA |
| **ON CHARACTERISTICS** (Note 3) | | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS}$ = $V_{DS}$, $I_D$ = 250 μA | | 1.0 | | 3.0 | V |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | | 6.4 | | mV/°C |
| Drain−to−Source On Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V | $I_D$ = 20 A | | 3.1 | 4.2 | mΩ |
| | | $V_{GS}$ = 4.5 V | $I_D$ = 20 A | | 5.0 | 6.5 | |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$ = 15 V, $I_D$ = 20 A | | | 21 | | S |
| **CHARGES, CAPACITANCES & GATE RESISTANCE** | | | | | | | |
| Input Capacitance | $C_{ISS}$ | $V_{GS}$ = 0 V, f = 1 MHz, $V_{DS}$ = 25 V | | | 2700 | | pF |
| Output Capacitance | $C_{OSS}$ | | | | 360 | | |
| Reverse Transfer Capacitance | $C_{RSS}$ | | | | 250 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS}$ = 4.5 V, $V_{DS}$ = 20 V; $I_D$ = 20 A | | | 25 | | nC |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS}$ = 10 V, $V_{DS}$ = 20 V; $I_D$ = 20 A | | | 51 | | |
| Threshold Gate Charge | $Q_{G(TH)}$ | $V_{GS}$ = 4.5 V, $V_{DS}$ = 20 V; $I_D$ = 20 A | | | 2.0 | | |
| Gate−to−Source Charge | $Q_{GS}$ | | | | 8.0 | | |
| Gate−to−Drain Charge | $Q_{GD}$ | | | | 12.7 | | |
| Plateau Voltage | $V_{GP}$ | | | | 3.2 | | V |
| Gate Resistance | $R_G$ | | | | 1.2 | | Ω |
| **SWITCHING CHARACTERISTICS** (Note 4) | | | | | | | |
| Turn−On Delay Time | $t_{d(ON)}$ | $V_{GS}$ = 4.5 V, $V_{DS}$ = 20 V, $I_D$ = 10 A, $R_G$ = 1.0 Ω | | | 13 | | ns |
| Rise Time | $t_r$ | | | | 24 | | |
| Turn−Off Delay Time | $t_{d(OFF)}$ | | | | 27 | | |
| Fall Time | $t_f$ | | | | 8.0 | | |
| Turn−On Delay Time | $t_{d(ON)}$ | $V_{GS}$ = 10 V, $V_{DS}$ = 20 V, $I_D$ = 10 A, $R_G$ = 1.0 Ω | | | 10 | | ns |
| Rise Time | $t_r$ | | | | 18 | | |
| Turn−Off Delay Time | $t_{d(OFF)}$ | | | | 32 | | |
| Fall Time | $t_f$ | | | | 5.0 | | |
| **DRAIN−SOURCE DIODE CHARACTERISTICS** | | | | | | | |
| Forward Diode Voltage | $V_{SD}$ | $V_{GS}$ = 0 V, $I_S$ = 5 A | $T_J$ = 25°C | | 0.73 | 1.2 | V |
| | | | $T_J$ = 125°C | | 0.57 | | |
| Reverse Recovery Time | $t_{RR}$ | $V_{GS}$ = 0 V, dIS/dt = 100 A/μs, $I_S$ = 10 A | | | 28.6 | | ns |
| Charge Time | $t_a$ | | | | 14 | | |
| Discharge Time | $t_b$ | | | | 14.5 | | |
| Reverse Recovery Charge | $Q_{RR}$ | | | | 23.4 | | nC |

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

## TYPICAL CHARACTERISTICS

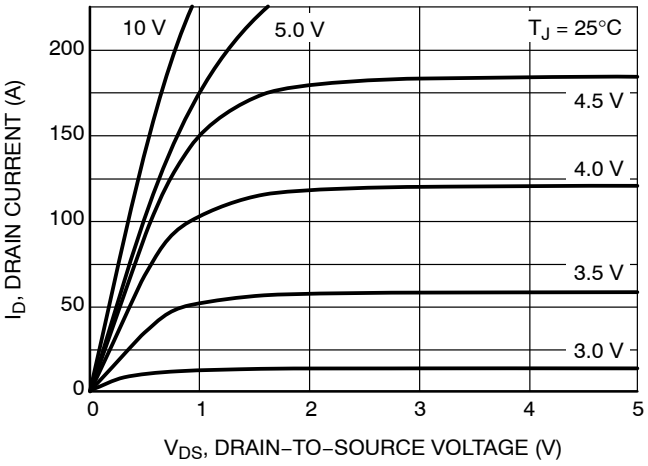



**Figure 1. On−Region Characteristics**

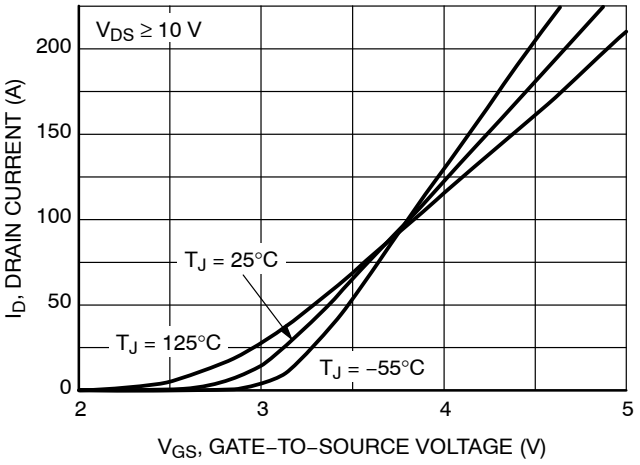



**Figure 2. Transfer Characteristics**

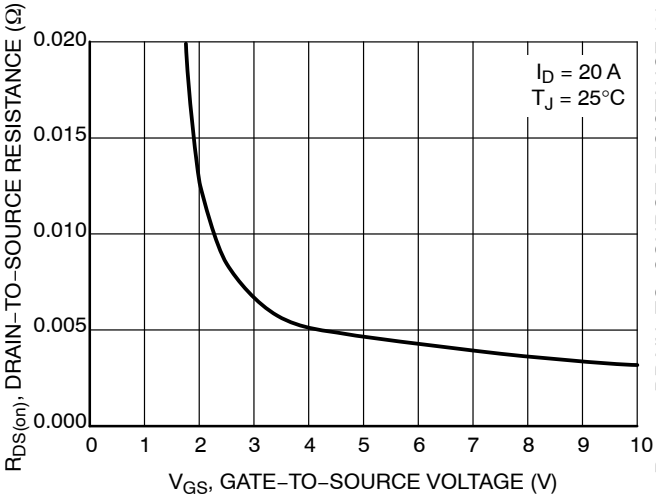



**Figure 3. On−Resistance vs. Gate−to−Source Voltage**

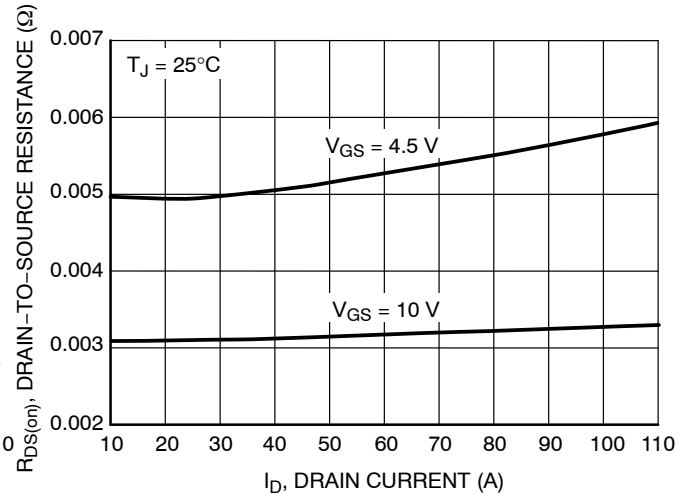



**Figure 4. On−Resistance vs. Drain Current and Gate Voltage**

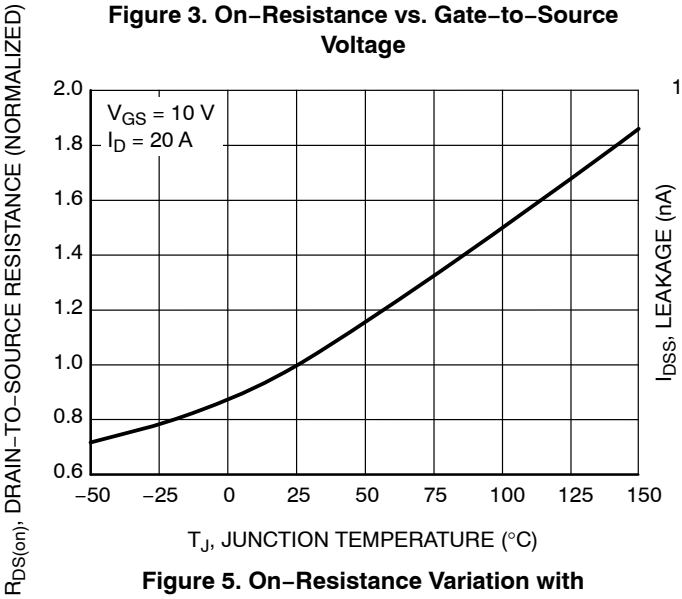



**Figure 5. On−Resistance Variation with Temperature**

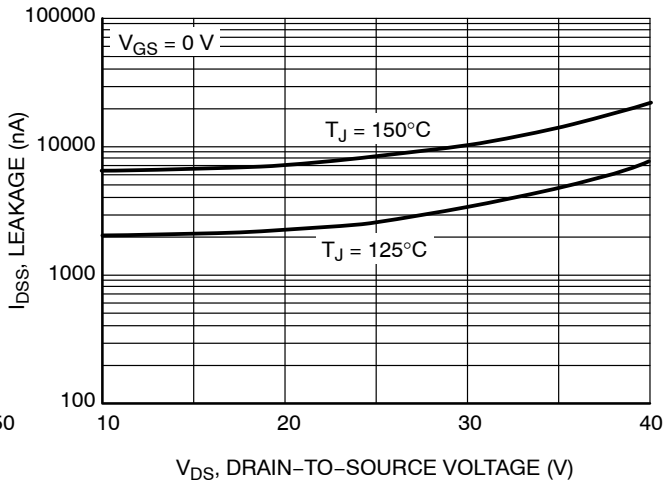



**Figure 6. Drain−to−Source Leakage Current vs. Voltage**

## TYPICAL CHARACTERISTICS

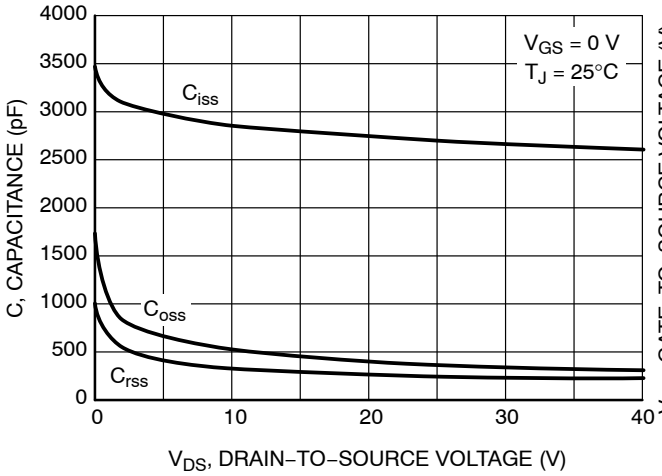



**Figure 7. Capacitance Variation**

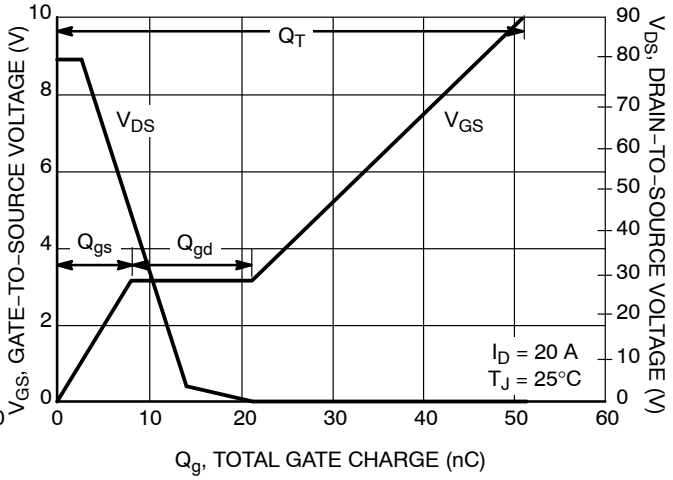



**Figure 8. Gate−to−Source Voltage vs. Total Charge**

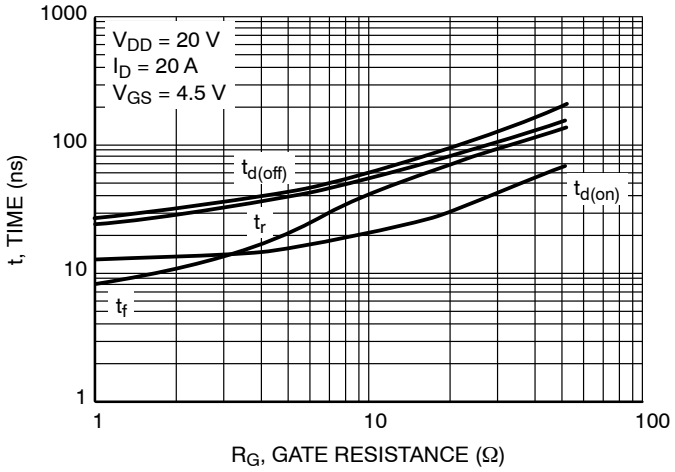



**Figure 9. Resistive Switching Time Variation vs. Gate Resistance**

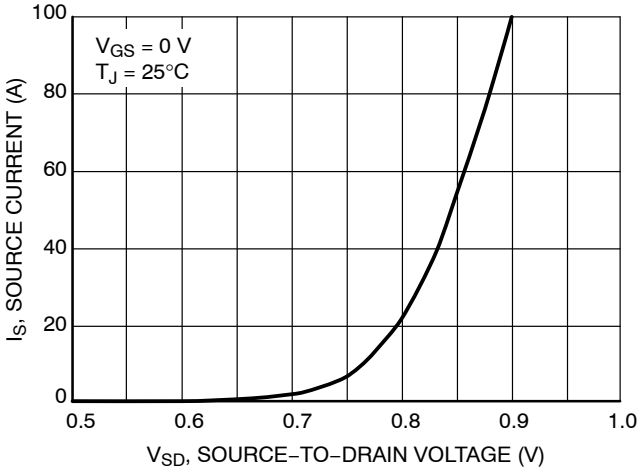



**Figure 10. Diode Forward Voltage vs. Current**

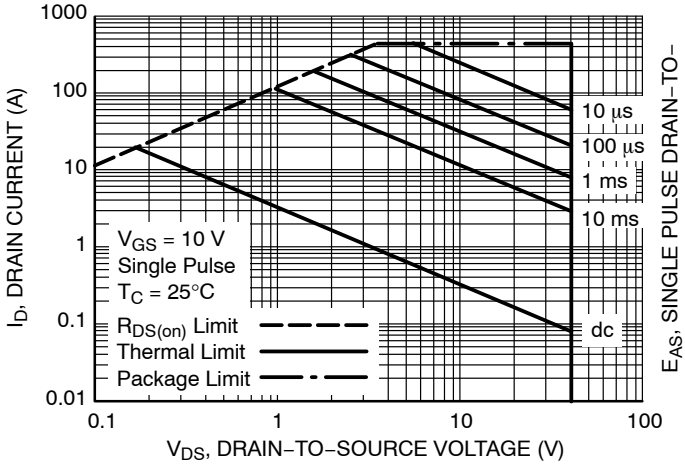



**Figure 11. Maximum Rated Forward Biased Safe Operating Area**

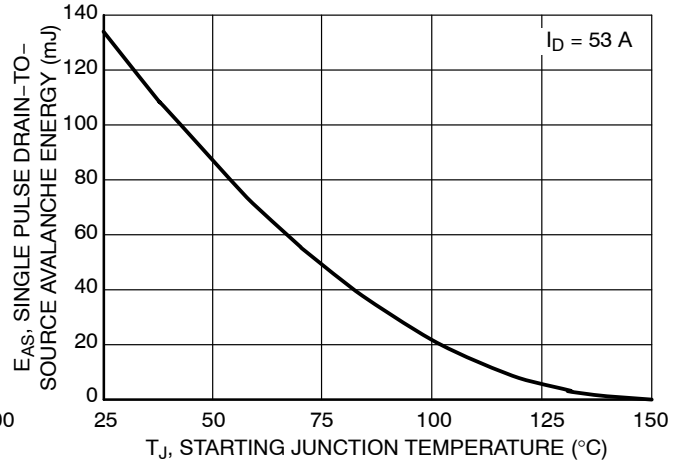



**Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature**

## TYPICAL CHARACTERISTICS

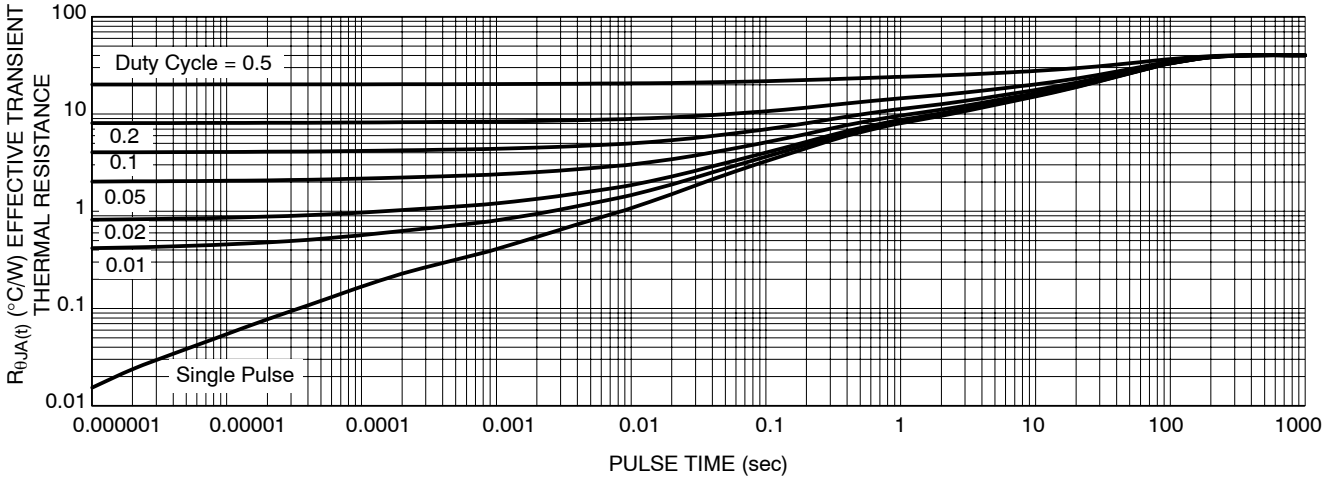
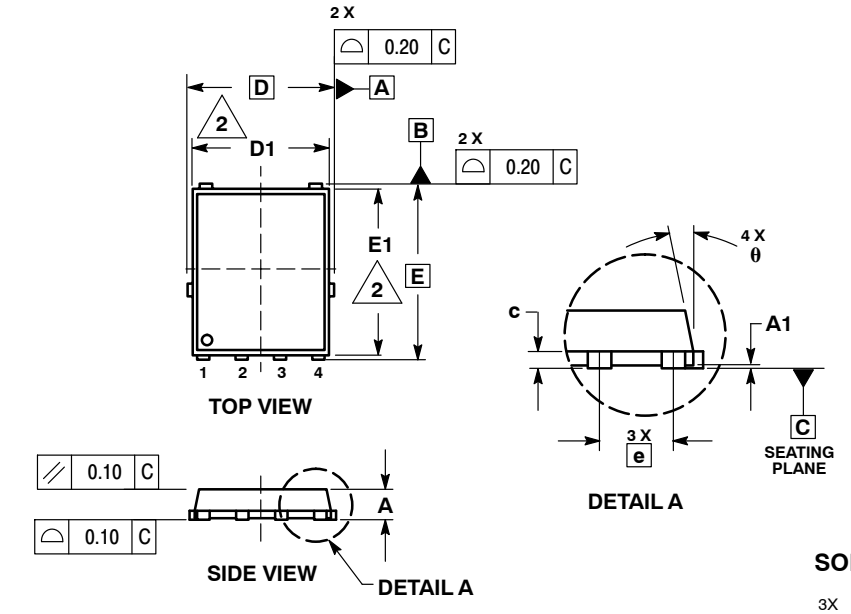



**Figure 13. Thermal Response**

## PACKAGE DIMENSIONS

**DFN5 5x6, 1.27P**
**(SO−8FL)**
CASE 488AA−01
ISSUE E

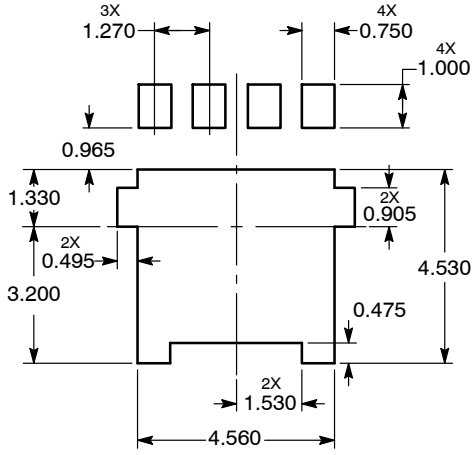



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

| | MILLIMETERS | | |
|---|---|---|---|
| DIM | MIN | NOM | MAX |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0.00 | −−− | 0.05 |
| b | 0.33 | 0.41 | 0.51 |
| c | 0.23 | 0.28 | 0.33 |
| D | | 5.15 BSC | |
| D1 | 4.50 | 4.90 | 5.10 |
| D2 | 3.50 | −−− | 4.22 |
| E | | 6.15 BSC | |
| E1 | 5.50 | 5.80 | 6.10 |
| E2 | 3.45 | −−− | 4.30 |
| e | | 1.27 BSC | |
| G | 0.51 | 0.61 | 0.71 |
| K | 0.51 | −−− | −−− |
| L | 0.51 | 0.61 | 0.71 |
| L1 | 0.05 | 0.17 | 0.20 |
| M | 3.00 | 3.40 | 3.80 |
| θ | 0 ° | −−− | 12 ° |

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN

### SOLDERING FOOTPRINT*




*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



**PUBLICATION ORDERING INFORMATION**

**LITERATURE FULFILLMENT**:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
**Phone**: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
**Fax**: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
**Email**: orderlit@onsemi.com

**N. American Technical Support**: 800−282−9855 Toll Free USA/Canada
**Europe, Middle East and Africa Technical Support:**
Phone: 421 33 790 2910
**Japan Customer Focus Center**
Phone: 81−3−5773−3850

**ON Semiconductor Website**: **www.onsemi.com**

**Order Literature**: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative